



PHK04P02T,518 Information



For Reference Only

Part Number PHK04P02T,518

Manufacturer Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET P-CH 16V 4.66A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PHK04P02T,518 Specifications

Manufacturer Part Number PHK04P02T,518 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 16V Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id 600mV @ ImA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 5W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 16V Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ##RU FET Feature Power Dissipation (Max) SW (Tc) Rds On (Max) @ Id, Vgs 120 mohm @ 1A, 4.5V Operating Temperature Surface Mount Supplier Device Package Package / Case B-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	PHK04P02T,518
Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 16V Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id 600mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 5W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Nexperia USA Inc.
Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 16V Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id 600mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 5W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 16V Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id 600mV @ ImA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 5W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 16V Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id 600mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) 5W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs T.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Departing Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case MOSFET (Metal Oxide) 16V MOSFET (Metal Oxide) 16V 16V 16V 16V 16V 16V 16V 16	Series	-
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 4.66A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 2.5V, 10V Vgs(th) (Max) @ Id 600mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) #8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 600mV @ 1mA Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) #8V FET Feature Power Dissipation (Max) Kds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	16V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 7.2nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) FET Feature - Power Dissipation (Max) SW (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	4.66A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 528pF @ 12.8V Vgs (Max) ±8V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	2.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) EET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	600mV @ 1mA
Vgs (Max)±8VFET Feature-Power Dissipation (Max)5W (Tc)Rds On (Max) @ Id, Vgs120 mOhm @ 1A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	7.2nC @ 4.5V
FET Feature - Power Dissipation (Max) 5W (Tc) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	528pF @ 12.8V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 120 mOhm @ 1A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±8V
Rds On (Max) @ Id, Vgs120 mOhm @ 1A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	5W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	120 mOhm @ 1A, 4.5V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

PHK04P02T,518 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PHK04P02T,518 Payment Methods



















PHK04P02T,518 Shipping Methods













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